

ABSTRACT

VERY HIGH CAPACITANCE FILM CAPACITOR AND METHOD FOR THE
PRODUCTION OF SAME

The present invention relates in particular to a very high capacitance film capacitor (1) that comprises a dielectric layer (100) consisting of at least one dielectric film (100a,..., 100i), each dielectric film (100a,..., 100i) of this dielectric layer (100) having the following parameters: - a relative dielectric permittivity [ϵ_f^i] such that $\epsilon_f^i \geq 10$, - a thickness [e_f^i] such that $0.05 \mu\text{m} \leq e_f^i \leq 50 \mu\text{m}$, - a dielectric strength [E_f^i] such that $E_f^i \geq 50 \text{ V}/\mu\text{m}$, parameters in which "f" signifies "film" and $i \geq 1$, "i" designating the "ith" dielectric film (100i) of said dielectric layer (100), this dielectric layer (100) separating a first electronic charge carrier structure (200) from a second electronic charge carrier structure (300), these two structures having an opposite surface (S) separated by the dielectric layer(100).

[FIG. 1]